

Depletion-Mode Power MOSFET

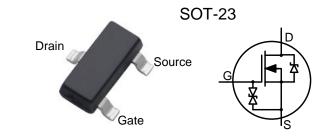
General Features

- ESD improved Capability
- > Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- ➤ Fast Switching Speed
- ➤ RoHS Compliant
- ➤ Halogen-free available

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- > Synchronous Rectification
- Normally-on Switches
- ➤ Linear Amplifier
- Converters
- Constant Current Source
- > Telecom

BV_{DSX}	R _{DS(ON)} (Max.)	$I_{ m DSS,min}$
150V	15 Ω	200mA



Ordering Information

Part Number Package		Marking	Remark
DMZ1521E	DMZ1521E SOT-23		Halogen Free

Absolute Maximum Ratings

T_A=25°C unless otherwise specified

Symbol	Parameter	DMZ1521E	Unit
V_{DSX}	Drain-to-Source Voltage ^[1]	150	V
V _{DGX}	Drain-to-Gate Voltage ^[1]	150	V
I_D	Continuous Drain Current	0.2	٨
I_{DM}	Pulsed Drain Current ^[2]	0.6	A
P_{D}	Power Dissipation	0.50	W
V_{GS}	Gate-to-Source Voltage	±20	V
T_{L}	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	${\mathbb C}$
T _J and T _{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	DMZ1521E	Unit
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	250	K/W



Electrical Characteristics

OFF Characteristics

 $T_A = 25$ °C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	150			V	V_{GS} =-15V, I_{D} =250 μA
				10	μΑ	$V_{DS} = 150V$, $V_{GS} = -15V$
$I_{D(OFF)}$	Drain-to-Source Leakage Current			1.0	mA	$V_{DS}=150V$, $V_{GS}=-15V$ $T_{J}=125$ °C
T	Gate-to-Source Leakage Current			20	η, Δ	$V_{GS} = +20V, V_{DS} = 0V$
I_{GSS}				-20	uA	V _{GS} =-20V, V _{DS} =0V

ON Characteristics

 $T_A = 25^{\circ}C$ unless otherwise specified

<u> </u>				А		ss outer wise specified
Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
I_{DSS}	Saturated Drain-to-Source Current	200			mA	$V_{GS} = 0V, V_{DS} = 25V$
R _{DS(ON)}	Static Drain-to-Source On-Resistance		10	15	Ω	$V_{GS}=0V$, $I_{D}=200mA^{[3]}$
$V_{\text{GS(OFF)}}$	Gate-to-Source Cut-off Voltage	-7		-5	V	$V_{DS} = 3V$, $I_D = 8 \mu A$
gfs	Forward Transconductance		0.24		S	$V_{DS} = 10V, I_D = 100mA$

Dynamic Characteristics

Essentially independent of operating temperature

Dynamic Characteristics				Discinding	шаерена	chi of operating temperature
Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
C _{ISS}	Input Capacitance		12.8			V _{GS} =-10V
Coss	Oput Capacitance		5.4		pF	$V_{DS}=25V$
C_{RSS}	Reverse Transfer Capacitance		3.3			$f=1.0MH_Z$
Q_{G}	Total Gate Charge		3			
Q _{GS}	Gate-to-Source Charge		0.23		nC	V_{GS} = -10V~0V V_{DS} =75V, I_{D} =200mA
Q_{GD}	Gate-to-Drain (Miller) Charge		1.1			

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time		7		no	
t _{rise}	Rise Time		16			$V_{GS} = -10V \sim 0V$
t _{d(OFF)}	Turn-off Delay Time		25		ns	$V_{DD} = 75V$, $I_D=200$ mA $R_G = 200$ hm
t_{fall}	Fall Time		120			



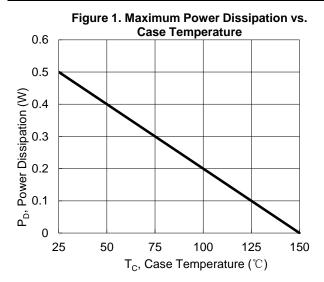


Source-Drain Diode Characteristics					T _A =25 °C	unless otherwise specified
Symbol	Parameter	Min Typ. Max. Units Test Condition			Test Conditions	
Ven	Diode Forward Voltage			1.2	V	$I_{cp} = 200 \text{ mA} \text{ V}_{cs} = -15 \text{ V}$

NOTE:

- [1] $T_J = +25^{\circ}C$ to $+150^{\circ}C$
- [2] Repetitive rating, pulse width limited by maximum junction temperature.
- [3] Pulse width \(380 \mu s; \) duty cycle \(\le 2\% \).





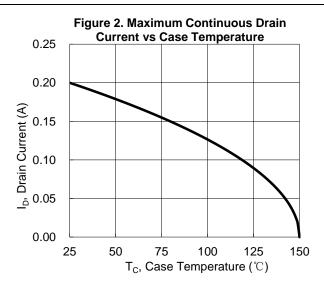


Figure 3. Typical Output Characteristics

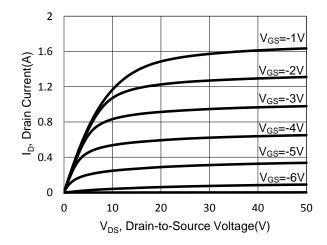
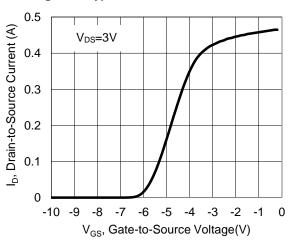
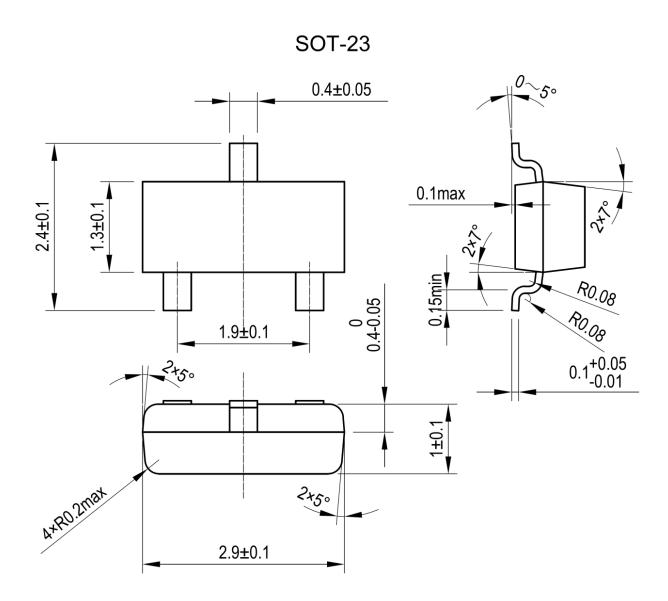


Figure 4. Typical Transfer Characteristics





Package Dimensions





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